Am100470

4096 x 1 IMOX[™] ECL Bipolar RAM

DISTINCTIVE CHARACTERISTICS

- Fast access time (12 ns typ.) improves system cycle
- Enhanced output voltage level compensation providing 6X (improvement in) VOL and VOH stability over supply and temperature ranges
- Internally voltage and temperature compensated providing flat AC performance
- Outputs preconditioned during write cycle eliminating write recovery glitch
- Emitter follower outputs easy wire-ORing
- Power dissipation decreases with increasing tempera-

GENERAL DESCRIPTION

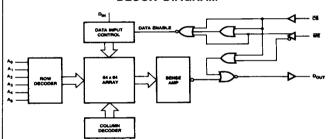
The Am100470 is a fully decoded 4096-bit ECL RAM organized 4096 words by one bit. Bit selection is achieved by means of a 12-bit address, A₀ through A₁₁. Easy memory expansion is provided by an active-LOW chip select (CS) input and an unterminated OR-tieable emitter follower output.

An active-LOW write line (WE) controls the write/read operation of the memory. When the chip select and write lines are LOW, the data input (DIN) is written into the addressed memory word simultaneously preconditioning the output so true data is present when the write cycle is complete. This preconditioning operation insures minimum write recovery times by eliminating the 'write recovery alitch."

Reading is performed with the chip select line LOW and the write line HIGH. The information stored in the addressed word is read out on the noninverting output (DOLIT).

During the writing operation or when the chip select line is HIGH, the output of the memory goes to a LOW state.





MODE SELECT TABLE

	Inpu	t	Output				
CS	WE	DIN	DOUT	Mode			
Н	Х	Х	L	Not Selected			
L	L	L	L	Write "0"			
L	L	Н	L	Write "1"			
L	Н	Х	DOLLT	Read			

H = HIGH = -0.9 VL = LOW = -1.7 VX = Don't Care

BD000660

PRODUCT SELECTOR GUIDE

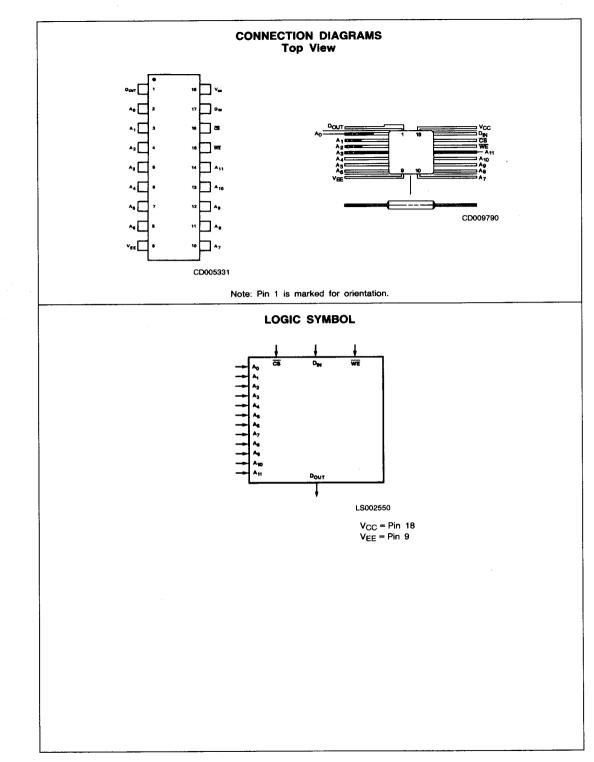
Highlights of Key Performance Parameters (Commercial)

Part Number	Am100470SA	Am100470A
Address Access Time (t _{AA})	15 ns	25 ns
Write Puise Width (tw)	15 ns	20 ns
Write Recovery (twR)	8 ns	10 ns
Chip Select Access/ Recovery and Write Disable Times (t _{ACS} , t _{RCS} , t _{WS})	8 ns	10 ns
Power Supply (I _{EE})	230 mA	200 mA

IMOX is a tradement of Advanced Micro Devices, Inc.

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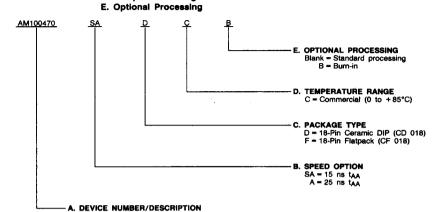


ORDERING INFORMATION

Standard Products

AMD standard products are available in several packages and operating ranges. The order number (Valid Combination) is formed by a combination of: **A. Device Number**

- B. Speed Option (if applicable)
- C. Package Type
- D. Temperature Range



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Valid Combinations

Valid Combinations list configurations planned to be supported in volume for this device. Consult the local AMD sales office to confirm availability of specific valid combinations, to check on newly released combinations, and to obtain additional data on AMD's standard military grade products.

Am100470

ABSOLUTE MAXIMUM RATINGS

Storage Temperature65 to +150°C
Ambient Temperature with
Power Applied55 to +125°C
VEE Pin Potential to GND Pin7.0 V to +0.5 V
Input Voltage (DC)VEE to +0.5 V
Output Current (DC Output HIGH)30 mA to +0.1 mA

Stresses above those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent device failure. Functionality at or above these limits is not implied. Exposure to absolute maximum ratings for extended periods may affect device reliability.

OPERATING RANGES

Commercial (C) Devices	
Temperature 0 t	to +85°C
Supply Voltage5.7 V t	io -4.2 V

Operating ranges define those limits between which the functionality of the device is guaranteed.

DC CHARACTERISTICS V_{FF} = -4.5 V, V_{CC} = GND (Note 2)

Parameter Symbol	Parameter Description	Test Conditions		B (Note 3)	Typ. (Note 1)	A (Note 3)	Units
Voн	Output Voltage HIGH	VIN = VIHA OF VILB		-1025	-955	-880	m۷
VoL	Output Voltage LOW	- THE THAT OF THE	Loading is	-1810	-1715	-1620	mV
Vohc	Output Voltage HIGH	V _{IN} = V _{IHB} or V _{ILA} 50 Ω to -2.0 V		-1035			m۷
Volc	Output Voltage LOW	7 1110 01 1110	THE ST TIES			-1610	mV
VIH	Input Voltage HIGH	Guaranteed Input Vol inputs (Note 4)	-1165		-880	mV	
V _{IL}	Input Voltage LOW	Guaranteed Input Vol inputs (Note 4)	-1810		-1475	m∨	
ін	Input Current HIGH	VIN = VIHA			220	μΑ	
IIL	Input Current LOW Chip Select(CS) All Other Inputs	V _{IN} = V _{ILB}	0.5 -50		170	μА	
	Power Supply Current	All Inputs and	Am100470A	-200 -160			mA
EE	(Pin 9)	Outputs Open Am100470SA		-230	-180		""

Notes: 1. Typical values are at $V_{EE} = -4.5V$, $T = 25^{\circ}C$ and maximum loading.

2. Output Load = 50 Ω and 30 pF to -2.0 V

 $T = T_A = 0$ to +85°C for DIPs. Guaranteed with transverse air flow exceeding 400 linear F.P.M. and 2-minute warm-up period. Typical resistance values of the package are:

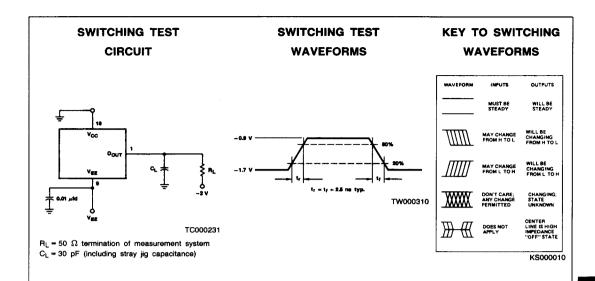
 $\theta_{\rm JA}$ (Junction to Ambient) = 90°C/Watt (still air)

 $\theta_{\rm JA}$ (Junction to Ambient) = 50°C/Watt (at 400 F.P.M. air flow)

 $T = T_C = 0$ to +85°C for Flatpacks and Leadless Chip Carriers.

 $\theta_{\rm JC}$ (Junction to Case) = 25°C/Watt

- 3. Definition of symbols and terms used in this product specification: The relative values of the specified conditions and limits will be referenced to an algebraic scale. The extremities of the scale are: "A" the value closest to positive infinity, "B" the value closest to negative infinity.
- 4. These are absolute voltages with respect to device ground pin and include all overshoots due to system and/or tester noise. Do not attempt to test these values without suitable equipment.



SWITCHING CHARACTERISTICS $V_{EE} = -4.73$ to -4.72 V (Note 2)

No.	Parameter Symbol	Parameter Description	Test Conditions	Am100470\$A			Am100470A			
				Min.	Typ. (Note 1)	Max.	Min.	Typ. (Note 1)	Max.	Units
READ	MODE									
. 1	tACS	Chip Select Access Time			6	8		8	10	ns
2	tRCS	Chip Select Recovery Time	Measured at 50% of input to 50% of output		6	8		8	10	ns
3	taa	Address Access Time	output		12	15		18	25	ns
WRITE	MODE				***					
4	tw	Write Pulse Width (to Guarantee Writing)	twsa = twsa(Min.)	15			20			ns
5	twsp	Data Setup Time Prior to Write	·	2			2			ns
6	twHD	Data Hold Time After Write		2			2			ns
7	twsa	Address Setup Time Prior to Write	tw = tw(Min.)	3			3		•	ns
8	twha	Address Hold Time After Write		2			2			ns
9	twscs	Chip Select Setup Time Prior to Write		2			2			ns
10	twncs	Chip Select Hold Time After Write	Measured at 50% of input to 50% of	2			2			ns
11	tws	Write Disable Time	output		6	8		8	10	ns
12	twn	Write Recovery Time			6	8	1	8	10	ns
RISE 7	TIME AND FAL	LTIME								
	tr	Output Rise Time	Measured between 20% and 80%		2.5			2.5	•	ns
	t _f	Output Fall Time	points		2.5			2.5	-	
CAPAC	CITANCE		•							
	CIN	Input Pin Capacitance	Measure with a		4	5		4	5	Τ_
	COUT	Output Pin Capacitance	Pulse Technique on a Sample Basis.		7	8		7	8	→ pF

